# N-Channel Enhancement Mode Field Effect Transistor

## Product Summary

| | |
|---|---|
| ǒ $V_{DS}$ | 60V |
| ǒ $I_D$ | 350mA |
| ǒ $R_{DS(ON)}$( at $V_{GS}$=10V) | 1.0ɋ |
| ǒ $R_{DS(ON)}$( at $V_{GS}$=4.5V) | 1.4ɋ |

## General Description

ǒ Trench Power MV MOSFET technology
ǒ Voltage controlled small signal switch
ǒ Low input Capacitance
ǒ Fast Switching Speed
ǒ Low Input / Output Leakage
ǒ Moisture Sensitivity Level 1
ǒ Epoxy Meets UL 94 V-0 Flammability Rating
ǒ Halogen Free

## Applications

ǒ Battery operated systems
ǒ Solid-state relays
ǒ Direct logic-level interface TTL/CMOS

### ƴ **Absolute Maximum Ratings** ($T_A$=25 unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|

Drain-source VoltagTmT/f*500.74 455.59 0.48001 2Q EG[51 450 G[(Dir)

## ƴ **Electrical Characteristics** (T$_J$=25 unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Static Parameter** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$= 0V, $I_D$=250εA | 60 | - | - | V |

Zero Gate VoltageHeaderf*193.25 759.1 50.1

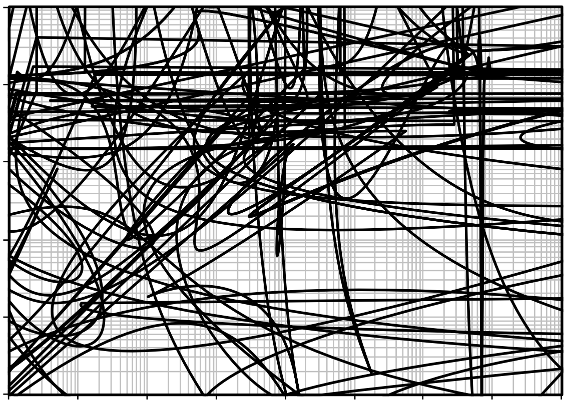


Figure 13. Maximum Transient Thermal Impedance

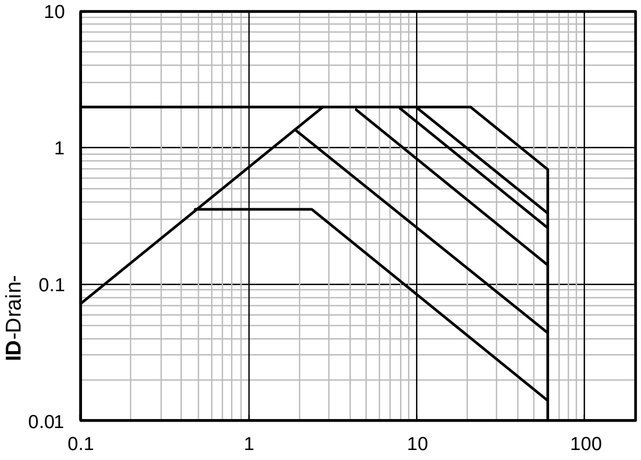


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

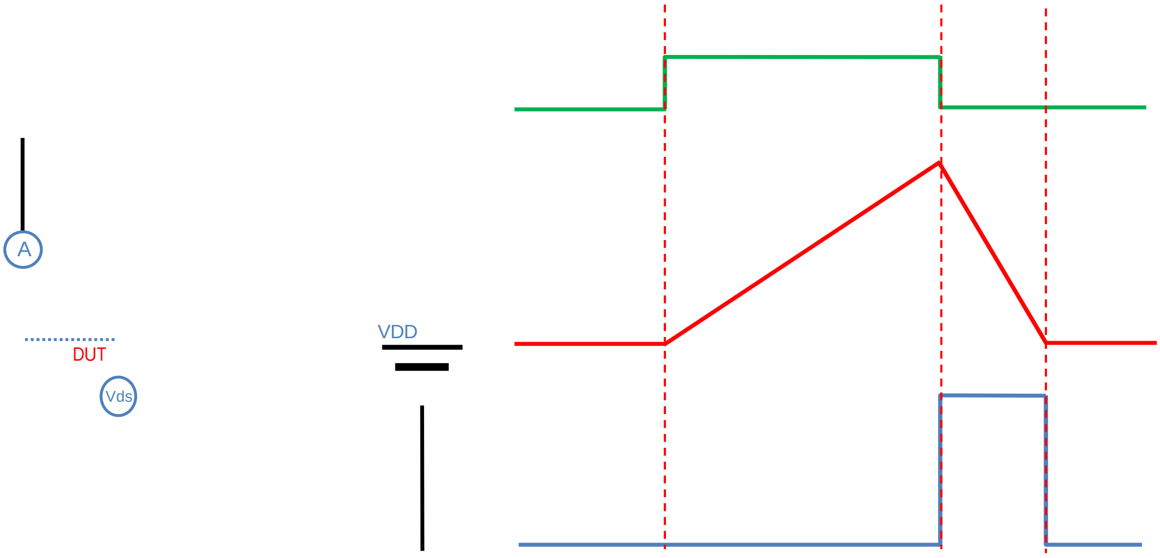
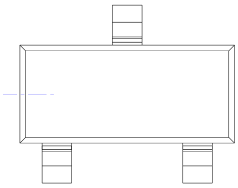
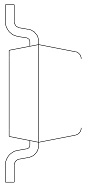
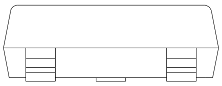


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

## √ SOT-23 Package information







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